## 大気圧化学気相合成法による WS2 成長に及ぼす WO3 前駆体と硫化過程の影響

Effect of WO<sub>3</sub> precursor and sulfurization process on WS<sub>2</sub> crystals growth by atmospheric pressure CVD technique

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Individual monolayers of metal dichalcogenides are atomically thin two-dimensional crystals have attracted significant interest owing to their direct-bandgap property for nano electronics and optoelectronics applications. In this prospect, controllable synthesis of high quality  $WS_2$  crystals by a chemical vapor deposition (CVD) process is of great importance. Here, we report the effect of sulfurization process and  $WO_3$  precursor on  $WS_2$  growth in an atmospheric pressure (AP) CVD. S powder was placed in the center of low temperature furnace and the  $WO_3$  (2 and 10 mg) powder spread on SiO<sub>2</sub>/Si substrate, which was kept in the small ceramic tube and placed in the center of high temperature furnace. S vapor was introduced with Ar flow rate of 80 sccm. Subsequently, the temperature of growth zone (SiO<sub>2</sub>/Si substrate with  $WO_3$  powder) was increased upto 750°C by the ramping rate 3°C min<sup>-1</sup>. The quantity of  $WO_3$  powder spread on SiO<sub>2</sub>/Si substrate significantly affect the nucleation and layer numbers of triangular-shaped  $WS_2$  crystals. Pyramid-like few-layers stacked structure of  $WS_2$  crystals are obtained from densely spread  $WO_3$  procursor and rate of sulfurization at 750°C.

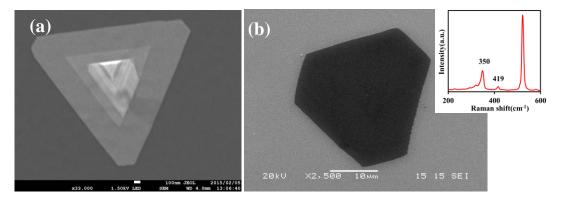


Fig. 1 FE-SEM image of pyramid like triangular crystal structure (b) SEM image of single triangular  $WS_2$  crystal (inset of the figure shows Raman spectra of the  $WS_2$  crystal)

## Reference

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- [2] A. Thangaraja, G. Kalita, M. Tanemura et al. Mater. Letts. 156, 156–160, (2015).